YJ Planar Schottky Barrier Diode Die Specification

200V 5A, 65mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB065H200SS-280A

Main Products Characterstics

- Average forward current: IF(AV) = 5 A
- Maximum operating junction temperature: Tj = 175 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

Maximum Ratings

Non−repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	120 A
Storage temperature re		
Maximum operating junction temperature	T_j	175 °C

Static Electrical Characteristics (Ta = 25°C)

		Value	
		Spec	**Typical**
		210 V	230V
Maximum forward voltage drop I_F = 5 A Pulse Test: tp = 300 μs, δ ≤ 2%	V_F	0.87V	0.83V
		5uA	0.2uA

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	60.6 Mils
Active Area	57 Mils
Top Metal	Ag
Back Metal	

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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